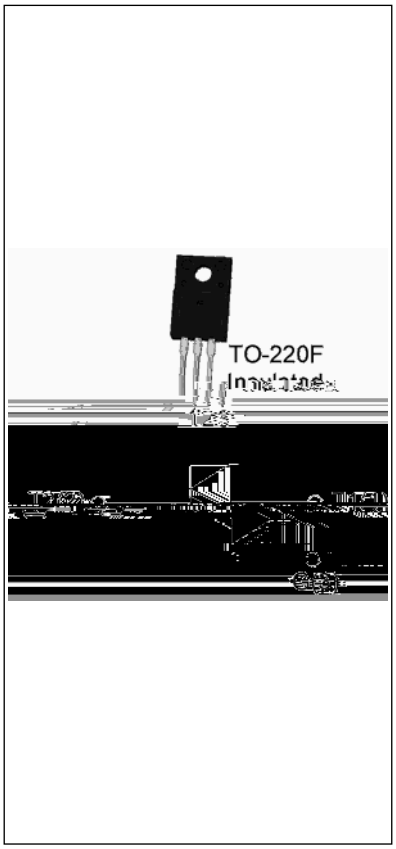
T1220H-6F 12A TRIAC

Rev.A.1.1

The T1220H-6F triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Compared to traditional triacs, T1220H-6F provides a very high switching capability up to junction temperatures of 150°C. By using an external plastic package, T1220H-6F provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM} /V_{RRM}	600	V
I_{GT} / /	20/20/20	mA

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-150	
Repetitive peak off-state voltage (T_j=25)	V_{DRM}	600	V
Repetitive peak reverse voltage (T_j=25)	V_{RRM}	600	V
RMS on-state current ($T_C \leq$ 106)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current (full cycle , t_p=20ms , T_j=25)	I_{TSM}	120	A
Non repetitive surge peak on-state current (full cycle , t_p=16.6ms , T_j=25)		132	
I^2t value for fusing (t_p=10ms , T_j=25)	I^2t	72	A^2s
Critical rate of rise of on-state current (I_G=2 × I_{GT} , f=100Hz , T_j=150)	dI/dt	100	A/μs
Peak gate current (t_p=20μs , T_j=150)	I_{GM}	4	A

Average gate power dissipation (T_j=150)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	4.5	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	20	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =150 R_L =3.3kΩ	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	25	mA
				55	
I_H	I_T =500mA		MAX.	25	mA
dV/dt	V_D=400V Gate Open T_j =150		MIN.	500	V/μs
(dI/dt)c	(dV/dt)c=20V/μs, T_j=150		MIN.	3	A/ms
t_{on}	I_G=40mA I_A=200mA I_R=20mA T_j=25		TYP.	3	μs
t_{off}				60	

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =17A t_p=380μs	T_j=25	1.4	V
V_{TO}	Threshold voltage	T_j=150	0.75	V
R_D	Dynamic resistance	T_j=150	37	mΩ
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25	5	μA
I_{RRM}		T_j=150	1.5	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2.8	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

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FIG.1: Maximum power dissipation versus RMS on-state current

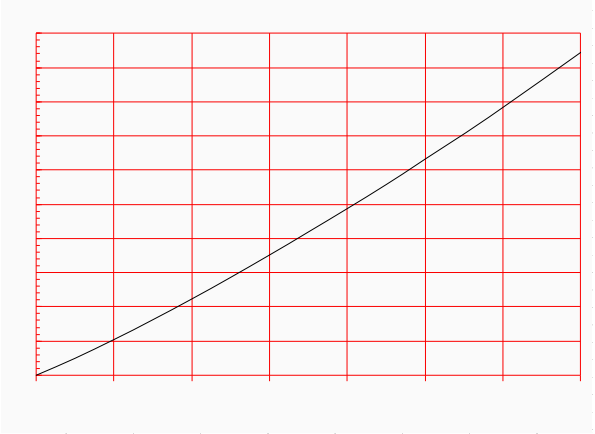


FIG.2: RMS on-state current versus case temperature

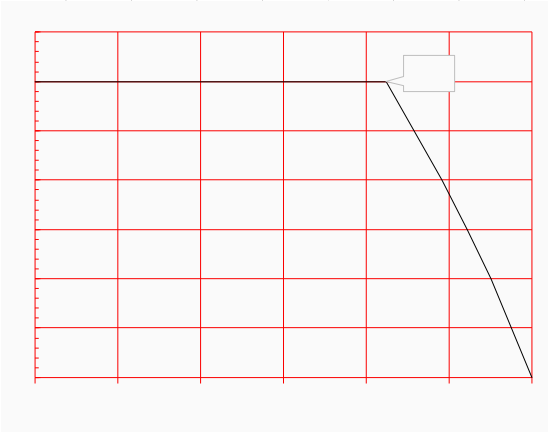


FIG.3: Surge peak on-state current versus number of cycles

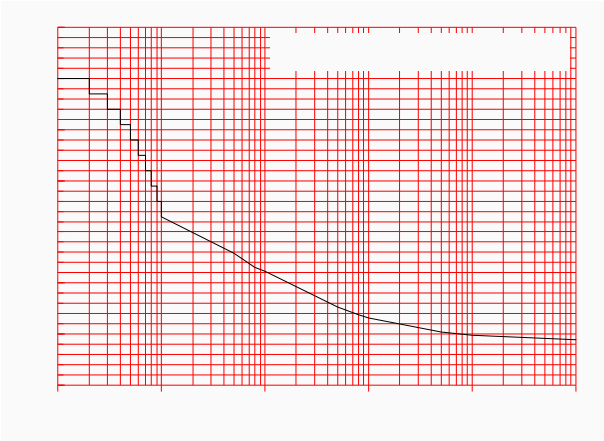


FIG.4: On-state characteristics

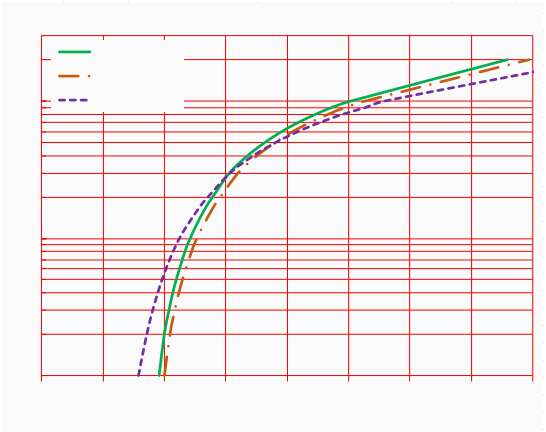


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width t_p<20ms, and corresponding value of I^2t (dI/dt<100A/μs)

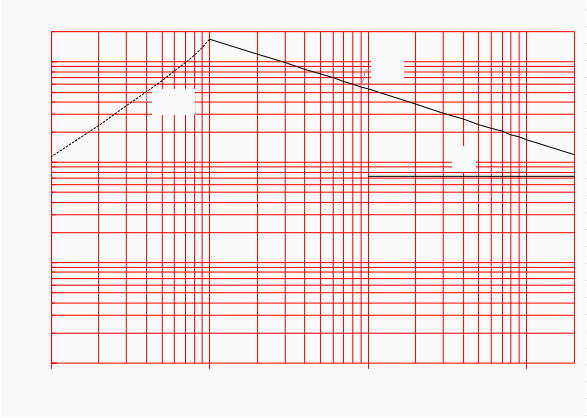
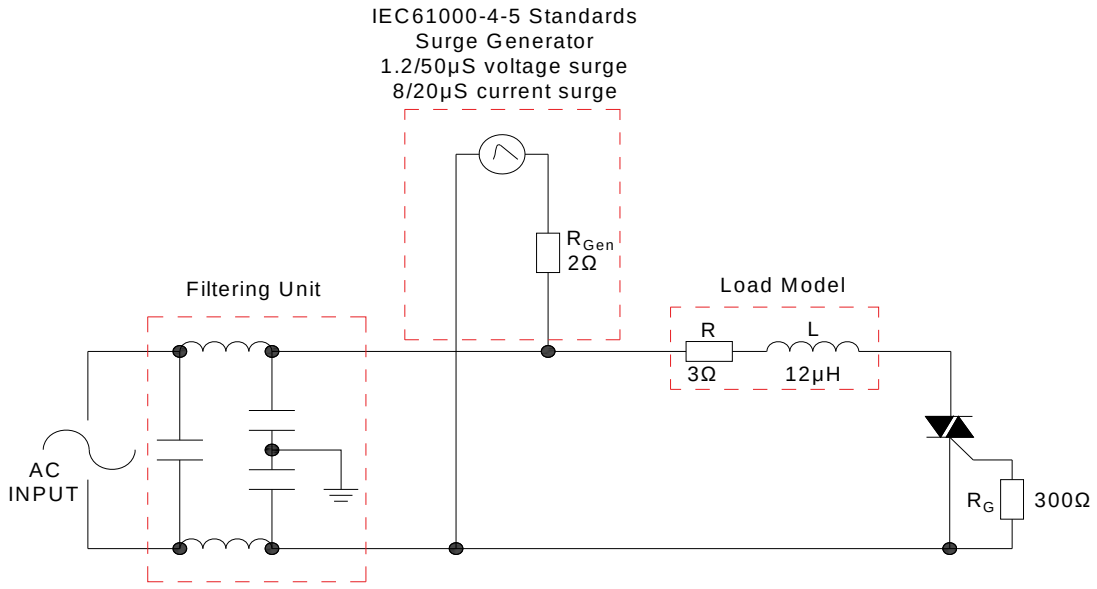


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)

Information furnished in this document is believed to be accura